

**REMARKS:**

Applicant has carefully studied the nonfinal Examiner's Action and all references cited therein. The amendment appearing above and these explanatory remarks are believed to be fully responsive to the Action. Accordingly, this important patent application is now believed to be in condition for allowance.

Applicant responds to the outstanding Action by centered headings that correspond to the centered headings employed by the Office, to ensure full response on the merits to each finding of the Office.

**Specification**

The Office has objected to the specification as failing to provide proper antecedent basis for the claimed subject matter. More specifically, the Office states that the specification lacks explicit basis for using ethanol in step (g), as in new claim 15.

In response, claim 15 has been cancelled.

**Claim Rejections – 35 U.S.C. § 112**

The Office has rejected claim 15 under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. More specifically, the Office states that the specification lacks explicit basis for using ethanol in step (g), as recited in claim 15.

In response, claim 15 has been cancelled.

**Claim Rejections – 35 U.S.C. § 102**

Applicant acknowledges the quotation of 35 U.S.C § 102(b).

Claims 1, 4-7, 9 and 11-12 stand rejected under 35 U.S.C § 102(b) as being clearly

anticipated by Ishida et al. (U.S. Patent No. 5,830,777). Applicant respectfully submits that Ishida et al. does not anticipate as the reference does not contain all the elements recited in the claims at bar.

Claim 1 has been amended to more clearly describe that with the Applicant regards as the invention.

Amended claim 1 describes a bulk silicon etching method comprising the following steps in the order named, including: (a) providing a silicon wafer; (b) diffusing the wafer with dopant, whereby the diffusion creates a PN-junction at a predetermined PN-junction depth throughout the surface of the wafer; (c) providing a mask; (d) positioning the mask in overlying relation to the surface of the wafer; (e) patterning a layer of oxide on the surface of the wafer, whereby the pattern of the oxide layer is defined by the mask; (f) etching the wafer to create recesses in the wafer in the areas that are not patterned with the oxide layer, whereby the etching step is sufficient to etch away the wafer to a depth below the PN-junction depth created by the diffusion step, thereby creating recessed areas having sidewalls, the sidewalls characterized by the presence of the PN-junction above the PN-junction depth and the absence of the PN-junction below the PN-junction depth; (g) hydrofluoric acid etching the wafer to form porous silicon thereon, whereby the porous silicon is formed in the sidewalls of the recessed areas characterized by the absence of the PN-junction; and (h) subjecting the wafer to wet etching resulting in dissolution of the porous silicon.

Applicant respectfully submits that Ishida et al. does not anticipate amended claim 1 because Ishida et al. does not describe the steps of the present invention in the order as claimed.

For the reasons cited above, Applicant believes that amended independent claim 1 is not anticipated by Ishida and is believed to be in condition for allowance.

Claims 4-14 are dependent upon claim 1, and are therefore allowable as a matter of law.

If the Office is not fully persuaded as to the merits of Applicant's position, or if an Examiner's Amendment would place the pending claims in condition for allowance, a telephone call to the undersigned at (813) 925-8505 is requested.

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Very respectfully,

**SMITH & HOPEN**

By: \_\_\_\_\_

Dated: March 16, 2007

Molly L. Sauter

USPTO Reg. No. 46,457

180 Pine Avenue North

Oldsmar, Florida 34677

(813) 925-8505

Agent for Applicants

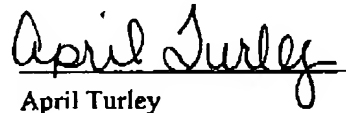
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**CERTIFICATE OF FACSIMILE TRANSMISSION**

(37 C.F.R. 1.8(a))

I HEREBY CERTIFY that this Amendment AF, including Amendments to the Claims, and Remarks is being transmitted by facsimile to the United States Patent and Trademark Office, Art Unit 1765, Attn.: Anita Karen Alanko, (571) 273-8300 on March 16, 2007.

Dated: March 16, 2007

  
April Turley